

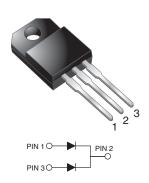
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## Vishay General Semiconductor

# **Dual Common Cathode Schottky Rectifier**

High Barrier Technology for Improved High Temperature Performance

#### ITO-220AB



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub> 2 x 15 A				
$V_{RRM}$	45 V			
I <sub>FSM</sub> 150 A				
V <sub>F</sub>	0.56 V			
I <sub>R</sub>	80 μΑ			
T <sub>J</sub> max.	x. 175 °C			
Package	ITO-220AB			
Circuit configuration	Common cathode			

#### **FEATURES**

- Power pack
- Guardring for overvoltage protection
- · Lower power losses, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106
- AEC-Q101 qualified available
  - Automotive ordering code: base P/NHE3
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, or polarity protection application.

### **MECHANICAL DATA**

Case: ITO-220AB

Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade Base P/NHE3\_X - RoHS-compliant, AEC-Q101 qualified ("\_X" denotes revision code, e.g. A,B,...)

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test, HE3 suffix meets JESD 201 class 2 whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs maximum

<b>MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER			MBRF30H45CT	UNIT
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	45	V
Working peak reverse voltage		$V_{RWM}$	45	V
Maximum DC blocking voltage		V <sub>DC</sub>	45	V
Maximum average forward rectified current (fig. 1)	total device		30	A
	per diode	I <sub>F(AV)</sub>	15	
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			150	А
Peak repetitive reverse surge current per diode at t <sub>p</sub> = 2 μs, 1 kHz			1.0	Α
Peak non-repetitive reverse energy (8/20 µs waveform)			25	mJ
Non-repetitive avalanche energy per diode at 25 °C, I <sub>AS</sub> = 4 A, L = 10 mH			80	mJ
Electrostatic discharge capacitor voltage human body model: C = 100 pF, R = 1.5 k $\Omega$			25	kV
Voltage rate of change (rated V <sub>R</sub> )			10 000	V/µs
Operating junction and storage temperature range			-65 to +175	°C
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min			1500	V

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	MBRF30H45CT		UNIT
Maximum instantaneous forward voltage per diode	I <sub>F</sub> = 15 A	T <sub>C</sub> = 25 °C	V <sub>F</sub> <sup>(1)</sup>	-	0.62	V
	I <sub>F</sub> = 15 A	T <sub>C</sub> = 125 °C		0.49	0.56	
	I <sub>F</sub> = 30 A	T <sub>C</sub> = 25 °C		-	0.73	
	I <sub>F</sub> = 30 A	T <sub>C</sub> = 125 °C		0.62	0.67	
Maximum reverse current per diode at working peak reverse voltage		T <sub>J</sub> = 25 °C	I <sub>R</sub> <sup>(2)</sup>	i	80	μA
		T <sub>J</sub> = 125 °C		5.0	15	mA

#### Notes

 $^{(1)}\,$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

(2) Pulse test: pulse width  $\leq$  40 ms

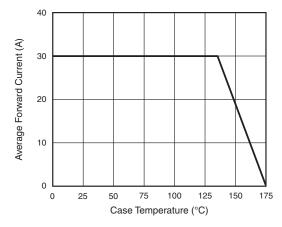
THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER	MBRF30H45CT	UNIT		
Typical thermal resistance junction to case per diode	$R_{ heta JC}$	4.5	°C/W	

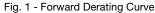
ORDERING INFORMATION (Example)						
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE	
ITO-220AB	MBRF30H45CT-E3/45	1.99	45	50/tube	Tube	
ITO-220AB	MBRF30H45CTHE3_A/P (1)	1.99	Р	50/tube	Tube	

#### Note

(1) AEC-Q101 qualified

### RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)





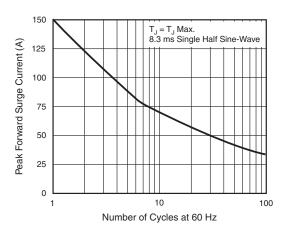


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode



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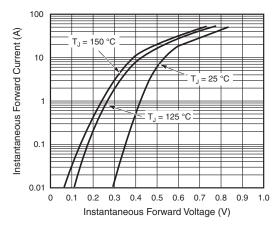


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

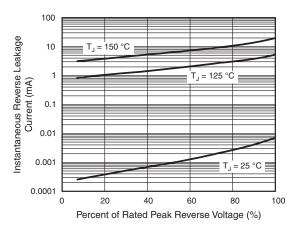


Fig. 4 - Typical Reverse Characteristics Per Diode

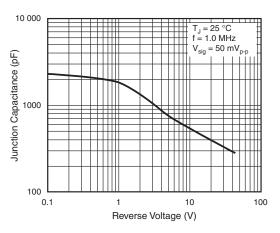


Fig. 5 - Typical Junction Capacitance Per Diode

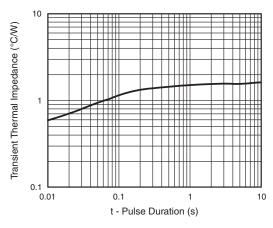
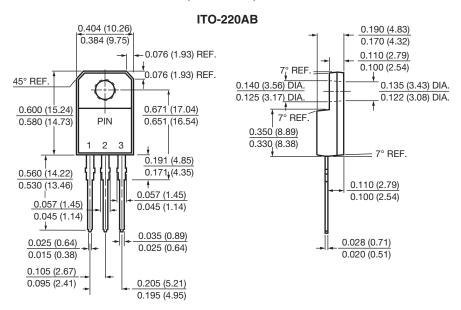


Fig. 6 - Typical Transient Thermal Impedance Per Diode

### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)



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